

# BUL741 BUL741FP

## High voltage fast-switching NPN power transistors

## Features

- High voltage capability
- Low spread of dynamic parameters
- Minimum lot-to-lot spread for reliable operation
- Very high switching speed

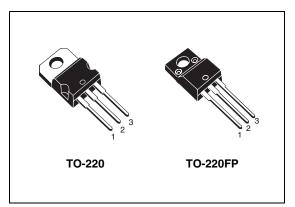
## Applications

- Electronic ballast for fluorescent lighting
- Switch mode power supplies.

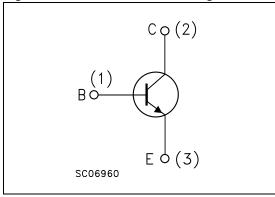
## Description

The devices are manufactured using high voltage multi-epitaxial planar technology for high switching speeds and high voltage capability.

Thanks to an increased intermediate layer, it has an intrinsic ruggedness which enables the transistor to withstand an high collector current level during breakdown condition, without using the transil protection usually necessary in typical converters for lamp ballast.



### Figure 1. Internal schematic diagram



#### Table 1. Device summary

Order codes	codes Marking Packages		Packaging	
BUL741	BUL741	TO-220	Tube	
BUL741FP	BUL741FP	TO-220FP	Tube	

August 2009

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# 1 Electrical ratings

Table 2.	Absolute maximum rating		
Symbol	Parameter	Value	Unit
V <sub>CES</sub>	Collector-emitter voltage (V <sub>BE</sub> = 0)	1050	V
V <sub>CEO</sub>	Collector-emitter voltage (I <sub>B</sub> = 0)	400	V
$V_{\text{EBO}}$	Emitter-base voltage ( $I_C = 0$ , $I_B = 2 A$ , $t_P < 10ms$ )	V <sub>(BR)EBO</sub>	V
Ι <sub>C</sub>	Collector current	2.5	А
I <sub>CM</sub>	Collector peak current (t <sub>P</sub> < 5 ms)	5	Α
Ι <sub>Β</sub>	Base current	1.5	Α
I <sub>BM</sub>	Base peak current (t <sub>P</sub> < 5ms)	3	А
Б	Total dissipation at $T_c = 25 \text{ °C}$ for TO-220	60	w
P <sub>tot</sub>	Total dissipation at $T_c = 25 \text{ °C}$ for TO-220FP	30	
T <sub>stg</sub>	Storage temperature	-65 to 150	°C
Τ <sub>J</sub>	Max. operating junction temperature	150	°C

## Table 2. Absolute maximum rating

#### Table 3. Thermal data

Symbol	Parameter	TO-220	TO-220FP	Unit	
R <sub>thJC</sub>	Thermal resistance junction-case max	2.08	4.17	°C/W	

## 2 Electrical characteristics

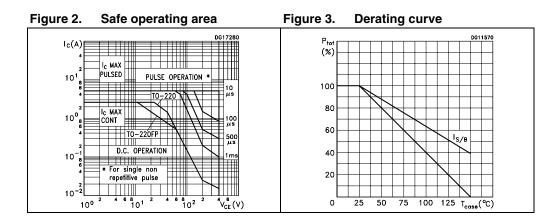
 $T_{case}$  = 25 °C unless otherwise specified.

		03				
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I <sub>CES</sub>	Collector cut-off current (V <sub>BE</sub> = 0)	V <sub>CE</sub> = 1050 V		0.2	10	μΑ
I <sub>CEO</sub>	Collector cut-off current $(I_B = 0)$	V <sub>CE</sub> = 400 V		10	250	μA
V <sub>(BR)EBO</sub> Emitter-base breakdown voltage (I <sub>C</sub> = 0)		I <sub>E</sub> = 1 mA	15	19	24	V
V <sub>CEO(sus)</sub> <sup>(1)</sup>	Collector-emitter sustaining voltage $(I_B = 0)$	I <sub>C</sub> = 10 mA	400	450		V
V <sub>CE(sat)</sub> <sup>(1)</sup>	Collector-emitter saturation voltage	$I_{\rm C} = 0.7 \text{ A } I_{\rm B} = 0.14 \text{ A}$ $I_{\rm C} = 2 \text{ A}$ $I_{\rm B} = 0.6 \text{ A}$		0.15 0.5	0.5 1.5	V V
V <sub>BE(sat)</sub> <sup>(1)</sup>	Base-emitter saturation voltage	$I_{\rm C} = 2  {\rm A}$ $I_{\rm B} = 0.6  {\rm A}$		1.1	1.5	V
h <sub>FE</sub>	DC current gain	$      I_{C} = 0.1 \ A \qquad \qquad V_{CE} = 5 \ V \\      I_{C} = 0.45 \ A \qquad \qquad V_{CE} = 3 \ V $	48 25	70 35	100 50	
t <sub>s</sub> t <sub>f</sub>	Resistive load Storage time Fall time			2.5 350	3.5 500	µs ns
E <sub>ar</sub>	Repetitive avalanche energy	$    L = 2 \text{ mH} \qquad C = 1.8 \text{ nF} \\ V_{BB(off)} = -5 \text{V} $	5			mJ

Table 4.Electrical characteristics

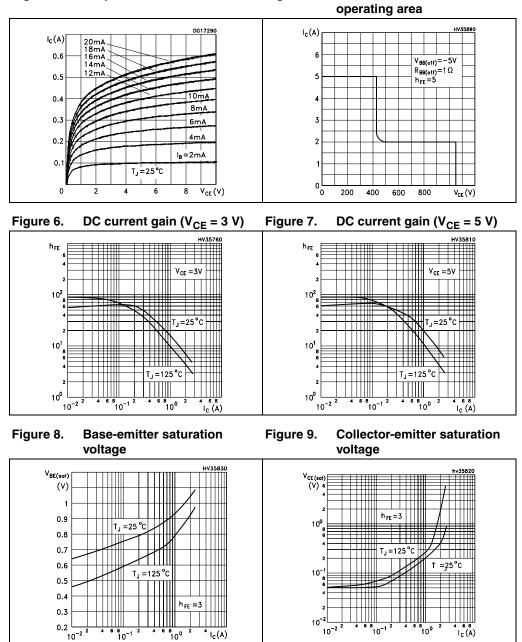
1. Pulse test: pulse duration  $\leq$ 300 µs, duty cycle  $\leq$ 2 %

## 2.1 Typical characteristic



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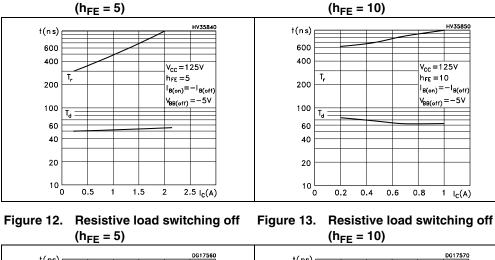
#### Figure 4. Output characteristics Figure 5. Reverse biased safe



Figure 10. Resistive load switching on

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Figure 11. Resistive load switching on



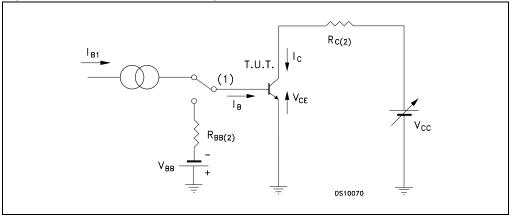
#### DG17560 DG17570 t(ns) t(ns) 6000 6000 4000 4000 t, 2000 2000 $V_{CC} = 125V I_{B(on)} = -I_{B(off)}$ $V_{BB(off)} = -5V h_{FE} = 10$ $\begin{array}{l} V_{CC} = 125V \quad I_{B(on)} = -I_{B(off)} \\ V_{BB(off)} = -5V \quad h_{FE} = 5 \end{array}$ 1000 1000 600 600 400 400 t, 200 200 100└─ 0 100└─ 0 0.5 1.5 2 2.5 I<sub>C</sub>(A) 0.2 0.4 0.6 0.8 1 I<sub>C</sub>(A)

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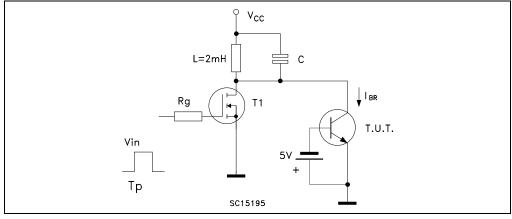
## 2.2 Test circuits

### Figure 14. Resistive load switching test circuit



- 1. Fast electronic switch
- 2. Non-inductive resistor

### Figure 15. Energy rating test circuit





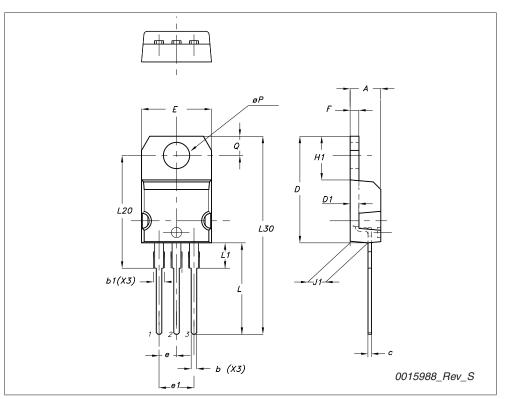
## **3** Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK<sup>®</sup> is an ST trademark.



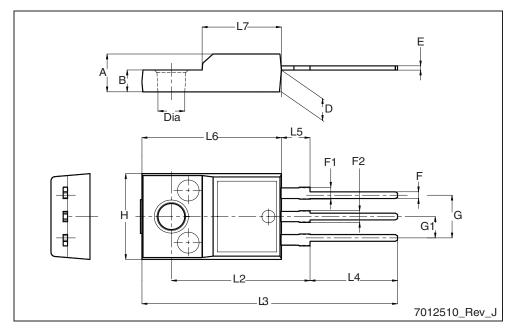
	mm		
Dim	Min	Тур	Max
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
С	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
е	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95







TO-220FP mechanical data					
Dim					
Dim.	Min.	Тур.	Max.		
A	4.4		4.6		
В	2.5		2.7		
D	2.5		2.75		
E	0.45		0.7		
F	0.75		1		
F1	1.15		1.70		
F2	1.15		1.5		
G	4.95		5.2		
G1	2.4		2.7		
Н	10		10.4		
L2		16			
L3	28.6		30.6		
L4	9.8		10.6		
L5	2.9		3.6		
L6	15.9		16.4		
L7	9		9.3		
Dia	3		3.2		







# 4 Revision history

#### Table 5.Document revision history

Date	Revision	Changes
11-Apr-2007	1	Initial release.
10-Jul-2007	2	Figure 12 and 13 have been updated.
18-Aug-2009	3	Added new package TO-220FP and mechanical data.



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